



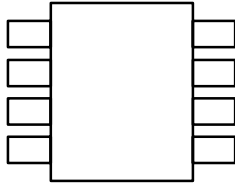
Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
30	0.022 at $V_{GS} = 10$ V	7.5
	0.030 at $V_{GS} = 4.5$ V	6.5

SCHOTTKY PRODUCT SUMMARY

V_{DS} (V)	V_{SD} (V) Diode Forward Voltage	I_F (A)
30	0.50 V at 1.0 A	2.0



FEATURES

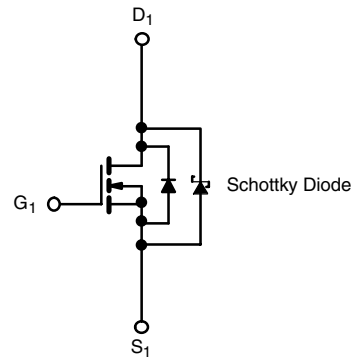
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- PWM Optimized
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



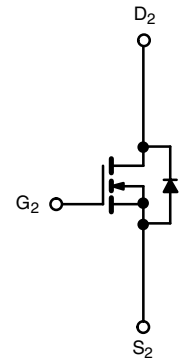
RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Symmetrical Buck-Boost DC/DC Converter



N-Channel MOSFET



N-Channel MOSFET

Ordering Information: Si4834BDY-T1-E3 (Lead (Pb)-free)

Si4834BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	7.5	5.7	A
	T _A = 70 °C		6.0	4.6	
Pulsed Drain Current		I _{DM}	30		
Continuous Source Current (Diode Conduction) ^a		I _S	1.7	0.9	W
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	2.0	1.1	
	T _A = 70 °C		1.3	0.7	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	MOSFET		Schottky		Unit
		Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^a	R_{thJA}	52	62.5	53	62.5	$^\circ\text{C/W}$
		93	110	93	110	
Maximum Junction-to-Foot (Drain)	R_{thJF}	35	40	35	40	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

MOSFET SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		0.8		3.0	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V				± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	Ch-1			100	μA
			Ch-2			1	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 85 °C	Ch-1			2000	
			Ch-2			15	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V		20			A
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 7.5 A			0.017	0.022	Ω
		V _{GS} = 4.5 V, I _D = 6.5 A			0.024	0.030	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 7.5 A			19		S
Diode Forward Voltage ^b	V _{SD}	I _S = 1 A, V _{GS} = 0 V	Ch-1		0.47	0.5	V
			Ch-2		0.75	1.2	
Dynamic ^a							
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 7.5 A			7	11	nC
Gate-Source Charge	Q _{gs}				2.9		
Gate-Drain Charge	Q _{gd}				2.5		
Gate Resistance	R _g			0.5	1.5	2.6	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 6 Ω			9	15	ns
Rise Time	t _r				10	17	
Turn-Off Delay Time	t _{d(off)}				19	30	
Fall Time	t _f				9	15	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.7 A, dl/dt = 100 A/μs	Ch-1		32	55	
			Ch-2		35	55	

Notes:

a. Guaranteed by design, not subject to production testing.

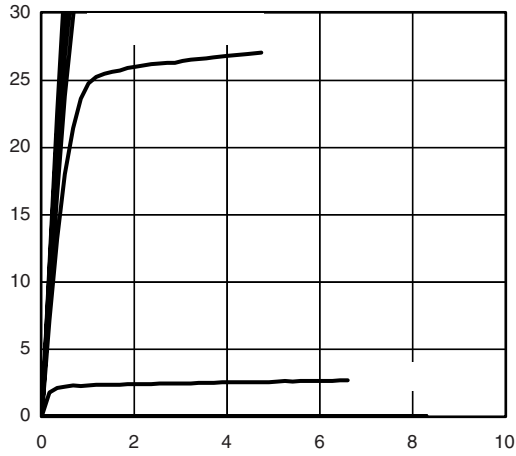
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

SCHOTTKY SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage Drop	V_F	$I_F = 1.0\text{ A}$		0.47	0.50	V
		$I_F = 1.0\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		0.36	0.42	
Maximum Reverse Leakage Current	I_{rm}	$V_R = 30\text{ V}$		0.004	0.100	mA
		$V_R = 30\text{ V}$, $T_J = 100\text{ }^{\circ}\text{C}$		0.7	10	
		$V_R = -30\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$		3.0	20	
Junction Capacitance	C_T	$V_R = 10\text{ V}$		50		pF

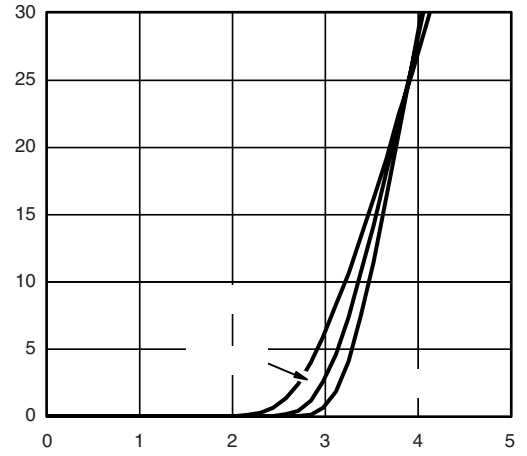
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



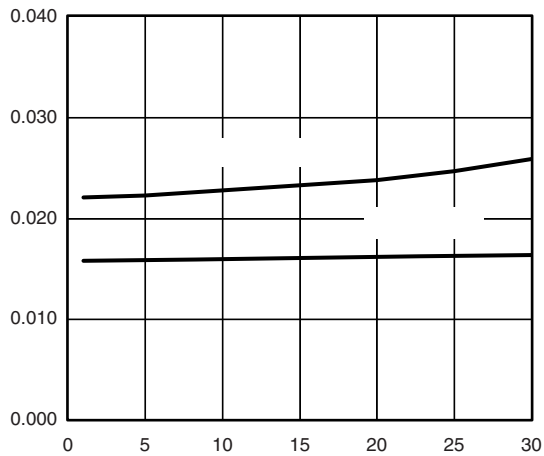
MOSFET TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



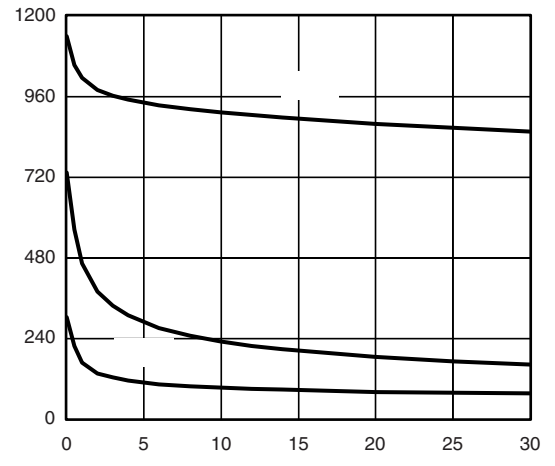
Output Characteristics



Transfer Characteristics

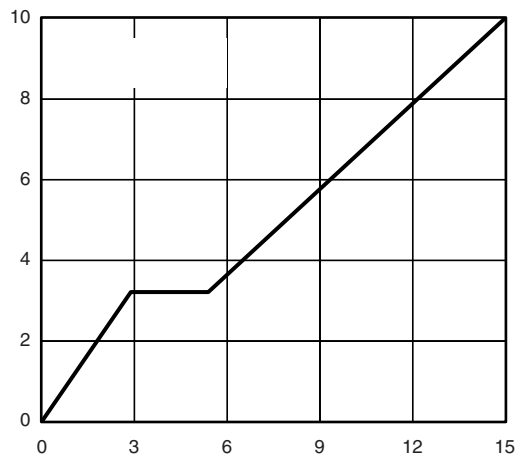


I_D - Drain Current (A)
On-Resistance vs. Drain Current

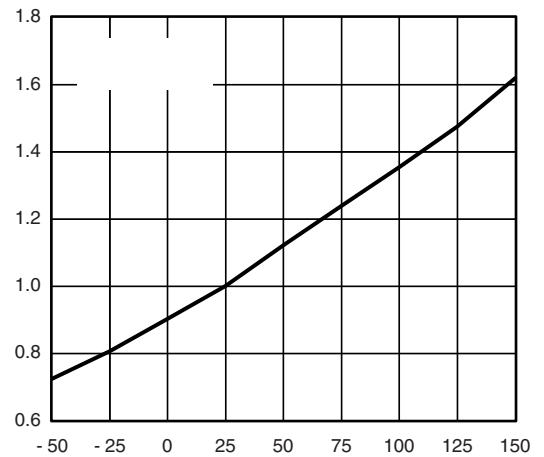


V_{DS} - Drain-to-Source Voltage (V)

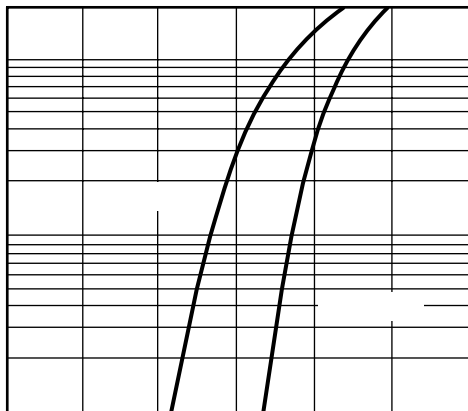
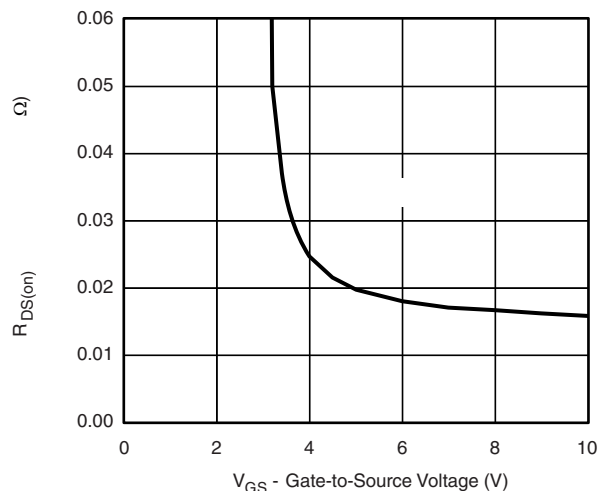
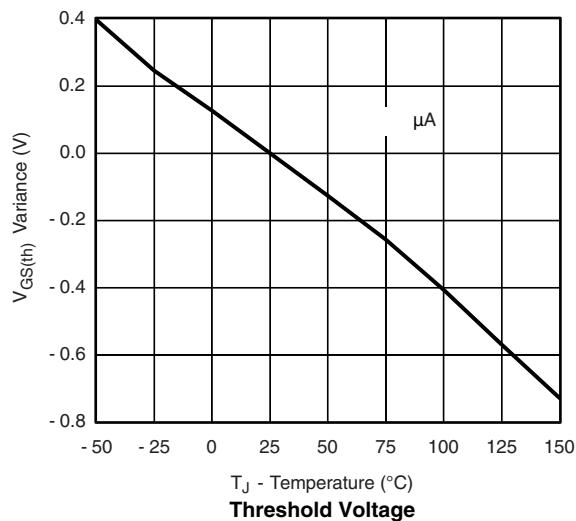
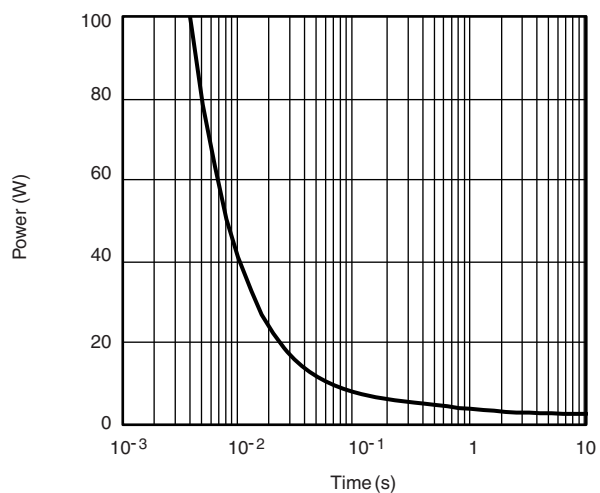
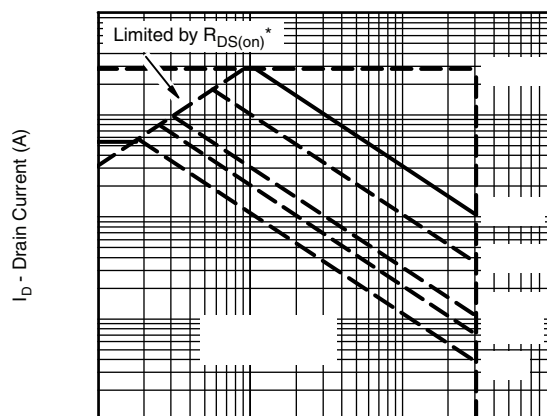
Capacitance



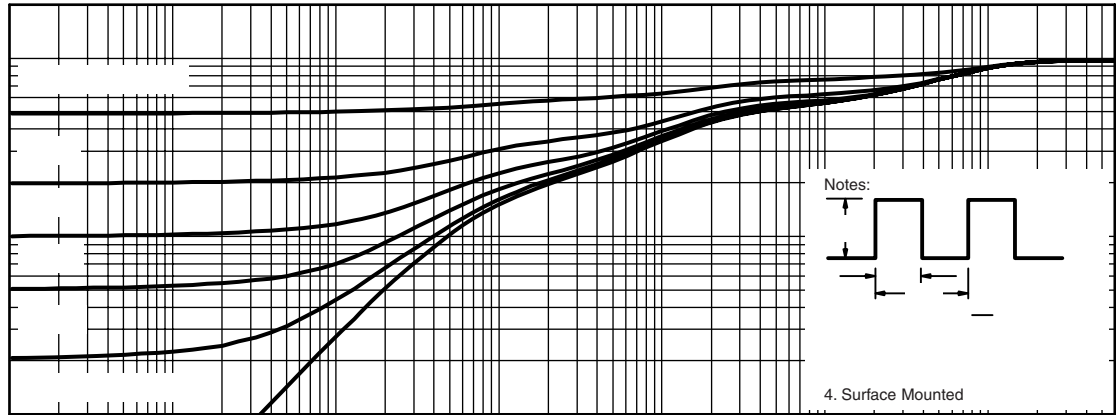
Gate Charge



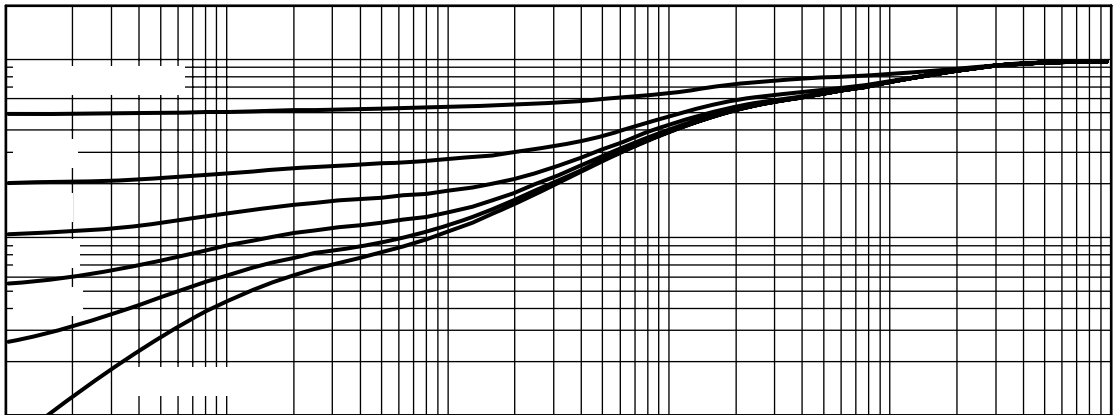
On-Resistance vs. Junction Temperature

MOSFET TYPICAL CHARACTERISTICS 25 °C unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient** V_{DS} - Drain-to-Source Voltage (V)* $V_{DS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area, Junction-to-Foot**

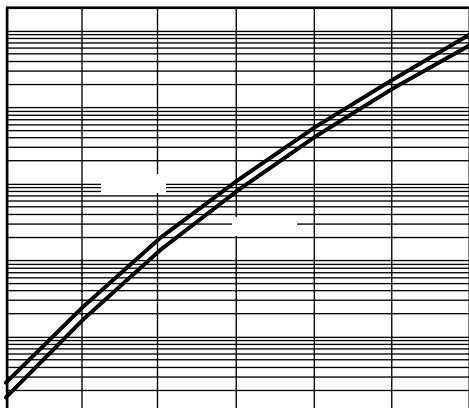
MOSFET TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



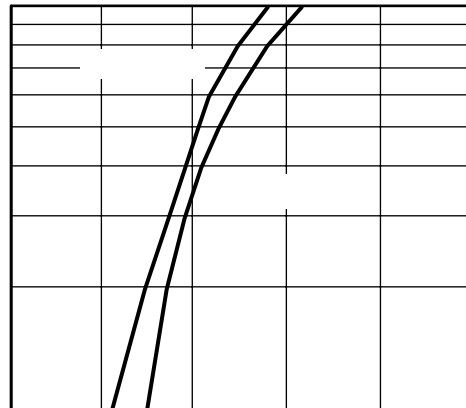
Normalized Thermal Transient Impedance, Junction-to-Ambient



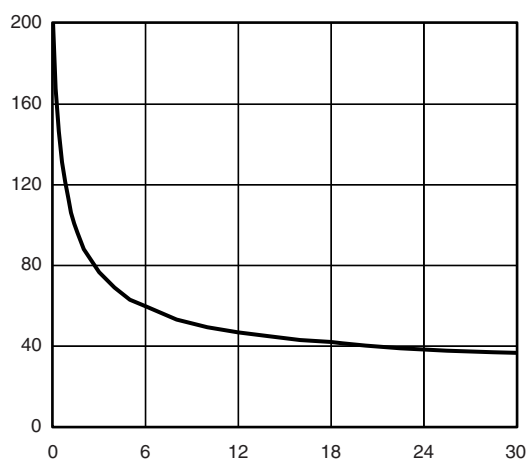
Normalized Thermal Transient Impedance, Junction-to-Foot

SCHOTTKY TYPICAL CHARACTERISTICS 25 °C unless otherwise noted

Reverse Current vs. Junction Temperature



Forward Voltage Drop



Capacitance

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